

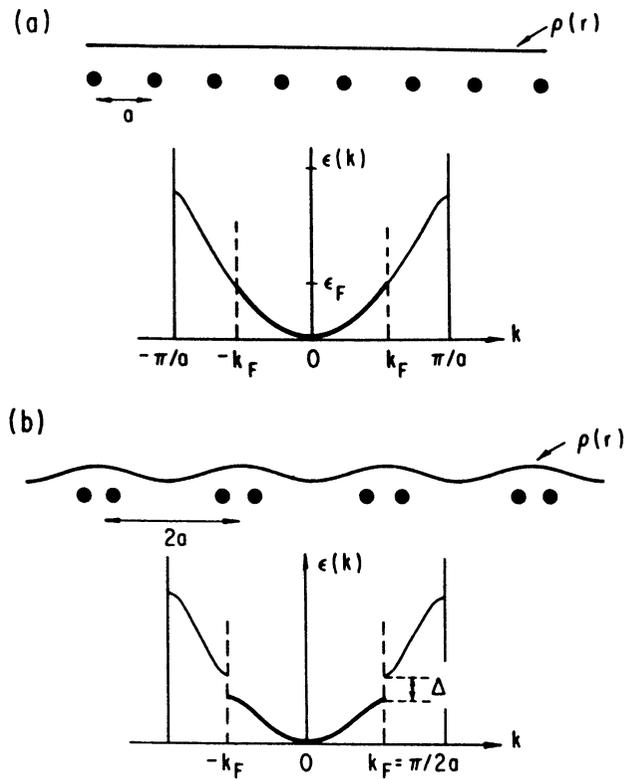
Spatial studies of charge-density-wave deformations

H. Requardt (ESRF/Grenoble)

- Peierls transition, sliding CDW
- how to study, earlier studies
- X-ray diffraction on CDW deformation

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Peierls-model:



1D metallic chain with e-phonon interaction:

unstable against modulation

=> charge-density-wave (CDW)

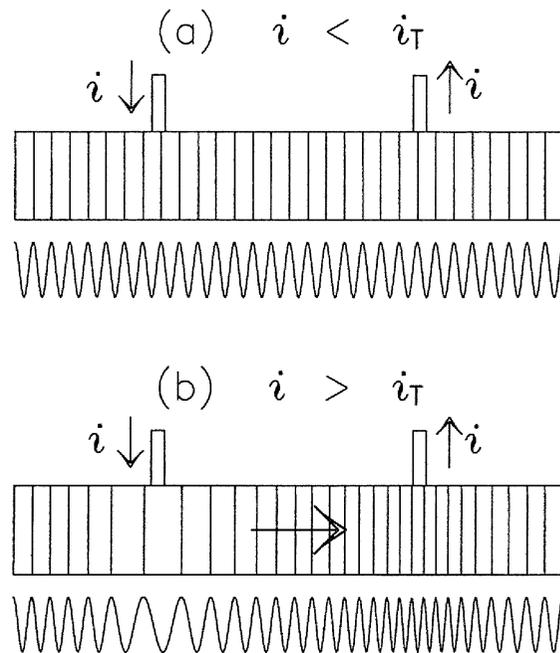
$$\rho(r) = \rho_0 + \Delta\rho \cdot \cos(2k_F r + \varphi)$$

defects: pinning of CDW phase φ

depinning by $E > E_T$

=> CDW slides, non-linear current

Sliding CDW:



(Fig.: Adelman et al., PRB **53** (1996) 1833)

- creation/annihilation of wavefronts at current contacts

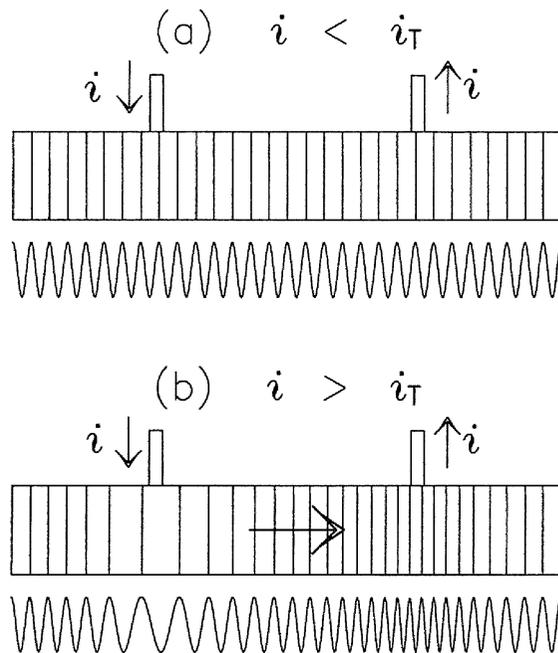
- conversion required:

normal current \Leftrightarrow condensed (CDW) current

=> phase slip

CDW elastically & plastically deformed

“How to study?”, “What to study?”



(Fig.: Adelman et al., PRB **53** (1996) 1833)

phase slip / current conversion located near current contacts

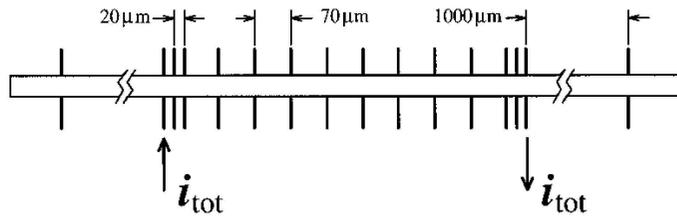
=> spatial dependence of CDW current:
 $j_{CDW}(x)$

=> adding/removing CDW wavefronts:
spatial dependence of CDW phase and
CDW wavelength:

$$Q_{CDW}(x) = Q_0 + q(x)$$

$$q(x) \propto \nabla \phi$$

a) electrical (multi-contact):



(Fig.: Adelman et al., PRB **53** (1996) 1833)

Measurement: $V(x)$ between neighboring contacts $\Rightarrow E(x)$ and $j_{CDW}(x)$

examples:

$j_{CDW}(x)$ in $NbSe_3$

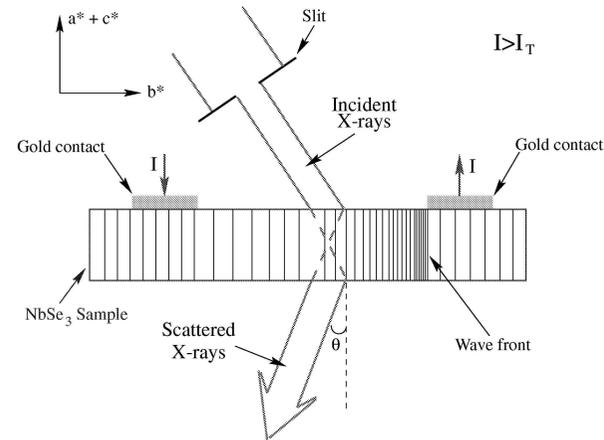
(Adelman et al., PRB **53** (1996) 1833)

$E(x)$ in $K_{0.3}MoO_3$

(Itkis et al., J.Phys. Cond.Matter **5** (1993) 4631)

b) "radiation":

X-ray diffraction



(Fig.: Rideau et al., EPL **56** (2001) 289)

Measurement: precise $q(x)$ of CDW-satellite reflection using narrow beam

examples: $NbSe_3$ DiCarlo et al., PRL **70** (1993) 845

Requardt et al., PRL **80** (1998) 5631

but also: IR-transmission

Measurement: integral IR-transmission through sample using narrow beam (30 μm)

example: $K_{0.3}MoO_3$

Itkis et al., PRB **52** (1995) R11545,

Synth. Metals **86** (1997) 1959

1st example: IR-transmission, $K_{0.3}MoO_3$ (Itkis et al.)

integral IR-transmission $\tau(x)$, $T=98K$
 changes by $\Delta\tau(x)$ when CDW is sliding

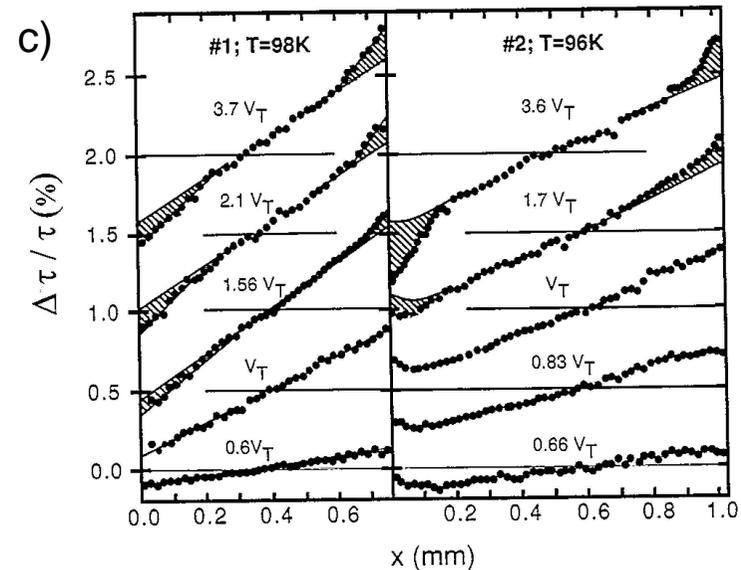
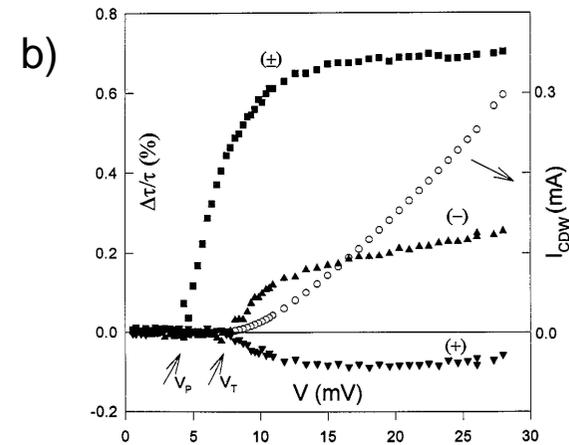
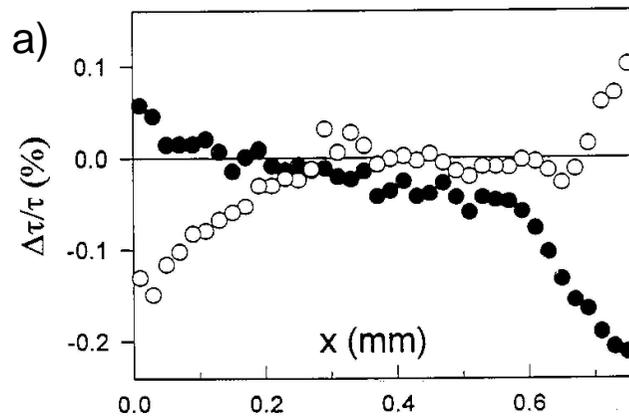
$$(\Delta\tau/\tau) \propto \nabla\phi$$

$\Delta\tau/\tau$ changes strongest near contacts

applying unipolar (+,-) and bipolar (\pm) pulses:

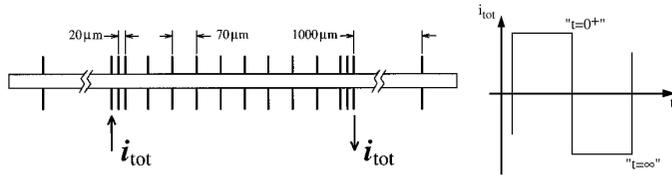
unipolar (a,b) => CDW slides when
 depinning at contacts

bipolar (b,c) => CDW depins first in bulk (V_P),
 then at contacts (V_T) and slides



Figs.: Itkis et al., Synth. Metals **86** (1997) 1959

2nd example: CDW-current j_{CDW} , NbSe₃ (Adelman et al.)



Spatially dependent voltage and resistivity measurements, $T=90K$

=> CDW current $j_C(x)$ and CDW-deformation $\nabla\phi(x)$

equations start with:

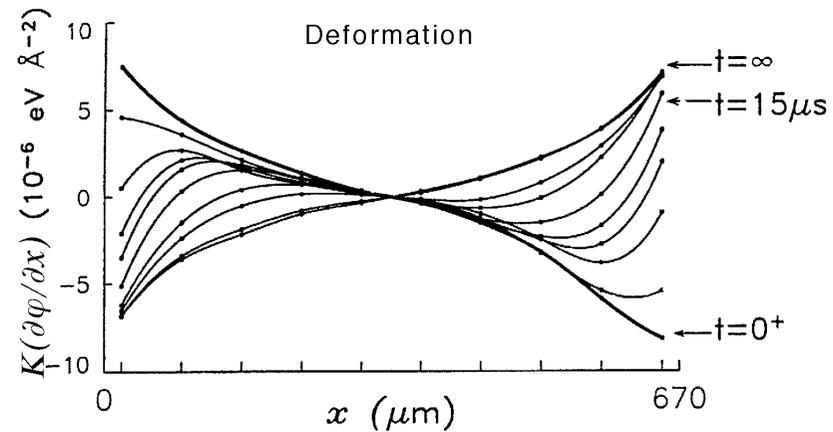
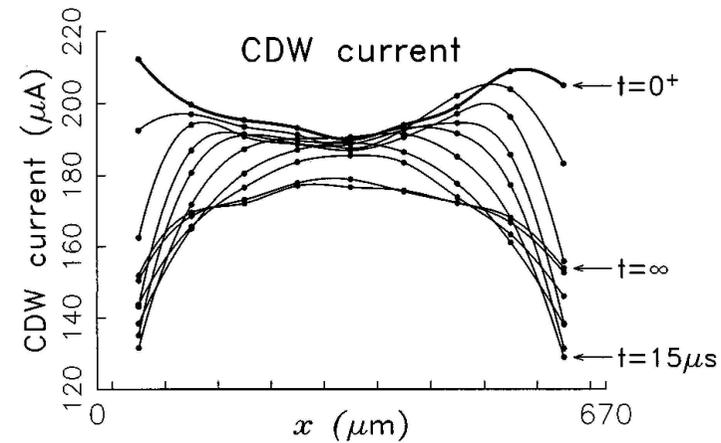
$$\text{Forces: } \gamma \frac{\partial \phi}{\partial t} = \left(\frac{en_C}{Q} \right) \cdot (E - E_P) + K \cdot \left(\frac{\partial^2 \phi}{\partial x^2} \right)$$

$$\text{Strain: } \varepsilon = \frac{1}{Q} \cdot \frac{\partial \phi}{\partial x}$$

Phase slip rate (homogeneous nucleation):

$$r_{PS}(x) = r_0 \cdot \exp\left(-\frac{en_C}{Q} \cdot \frac{V_a}{2QK\varepsilon(x)} \right)$$

$$i_C = \frac{1}{\rho_C + \rho_S} \cdot \left(\rho_S i_{tot} - E_P(i_C) + \left(\frac{en_C}{Q} \right)^{-1} K \frac{\partial^2 \phi}{\partial x^2} \right)$$



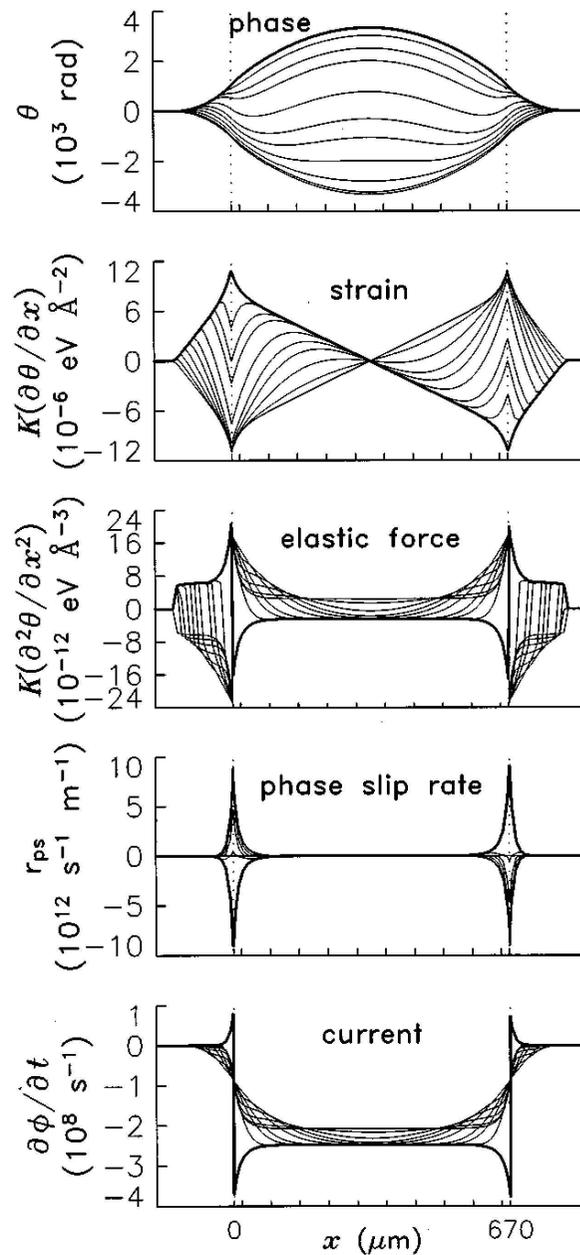
Figs.: Adelman et al., PRB **53** (1996) 1833

Adelman et al.:

taking parameters from experimental data $i_C(t,x)$ and equations

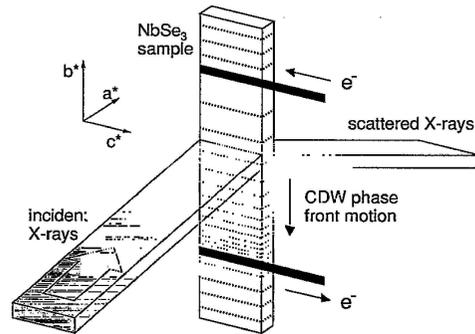
=> **Simulation of $i_C(t,x)$, $r_{ps}(t,x)$, $\tilde{N}_j(t,x)$ and $j(t,x)$**

=> CDW deformation essentially linear between current contacts with small nonlinear contribution due to phase slip; phase slip takes place in a very narrow section around current contacts



3rd example: X-ray diffraction, NbSe₃

1st study by DiCarlo et al. (PRL 70 (1993) 845) :



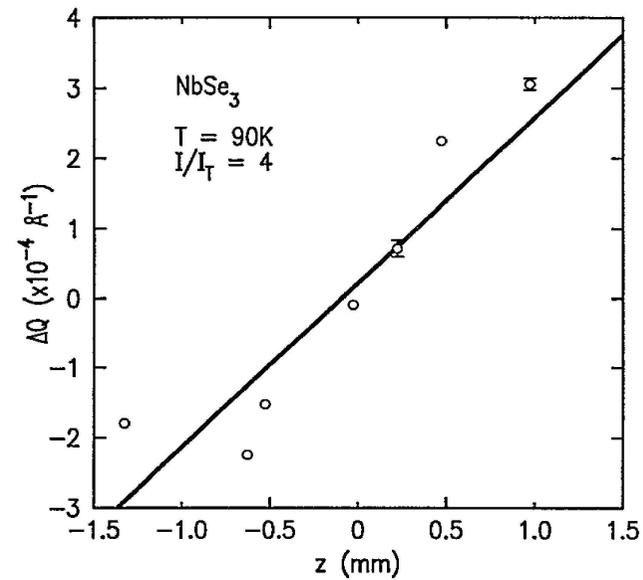
monitor shift ΔQ of CDW-satellite position Q along z ($\parallel \mathbf{b}^*$) applying depinning pulsed current

beam width: 800 μm

no data very close to current contacts

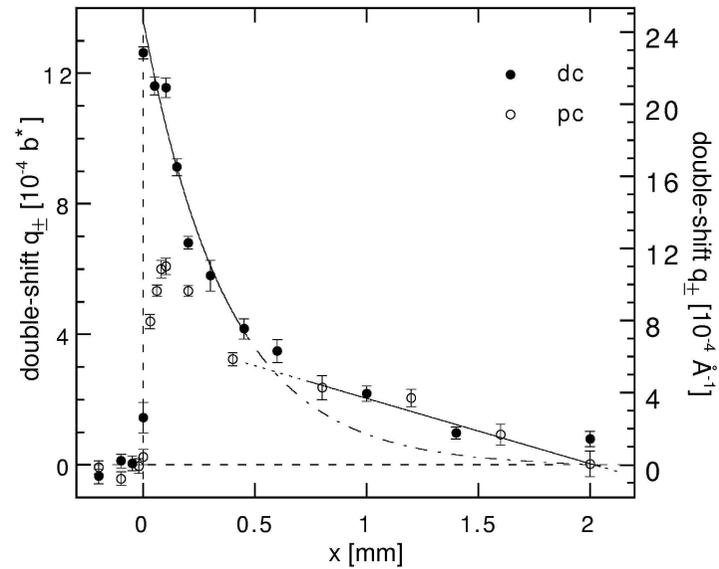
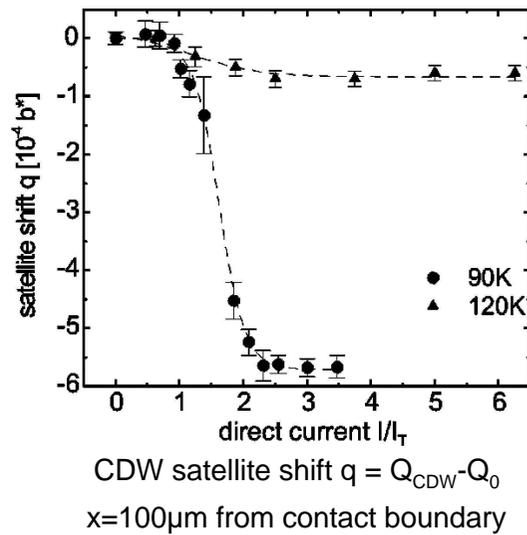
compare data with linear model by Ramakrishna et al. (PRL 68 (1992) 2066):

$$\Delta q(z) = \frac{\partial \phi}{\partial x} = \frac{e\rho_C}{QK_z} \cdot V_{PS} \cdot \frac{z}{L}$$



2nd study by Requardt et al. (PRL **80** (1998) 5631) :

- applying *dc* signal for steady state measurements on NbSe₃
- pulsed current (*pc*) data for comparison
- beam width 30-100μm
- data from sample centre to beyond contact boundary



$$90\text{K}, I = 2.13 \cdot I_T, q_{\pm} = Q_{CDW}(I>0) - Q_{CDW}(I<0)$$

2 regimes in *dc* $q(x)$ -profile:

- exponential decay from contact boundary to $x \approx 0.5$

length scale: $375 \pm 50 \mu\text{m}$

- linear decrease for $x > 0.7$

Brazovskii-model (PRB 61 (2000) 10640) , interpretation of results from Requardt et al.

considers disbalance between:

- condensed (CDW-) charge carriers (density $n_{\text{CDW}}=(1-\rho_i(T))n_i$) and
- non-condensed, “normal” charge carriers (density n_e)

μ_n = chem. potential of normal carriers

$$U = \left(\frac{1}{\pi} \nabla \varphi \right) / N_F^i + \Phi \quad \text{stress of CDW}$$

(Φ = potential from external electrical field,

N_F^i = DOS of “condensible” charge carriers)

$$\eta = \mu_n - U \propto q$$

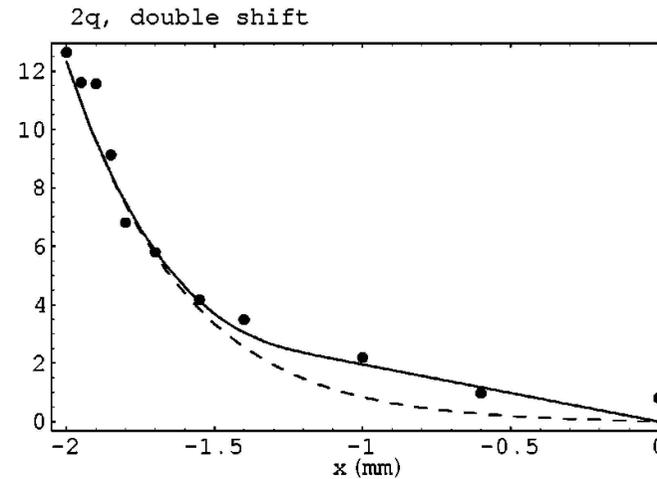
further “ingredient” of model:

carrier conversion $r_{\text{PS}}(\eta) = \nabla j_{\text{CDW}}$

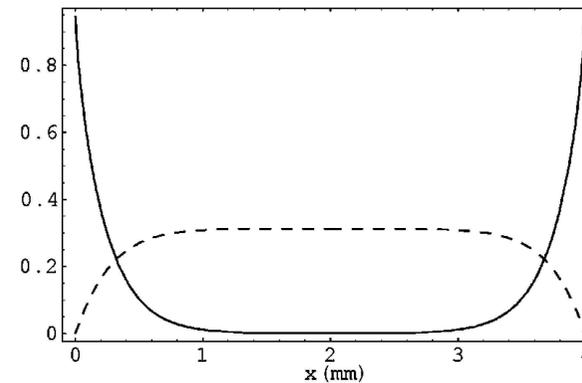
- homogeneous: $r_{\text{PS}} \propto \exp(-\eta_0/|\eta|)$
- heterogeneous: e.g. $r_{\text{PS}} \propto \eta$
- “active”: $r_{\text{PS}} \propto j_{\text{CDW}}$

assuming heterogeneous and active conversion:

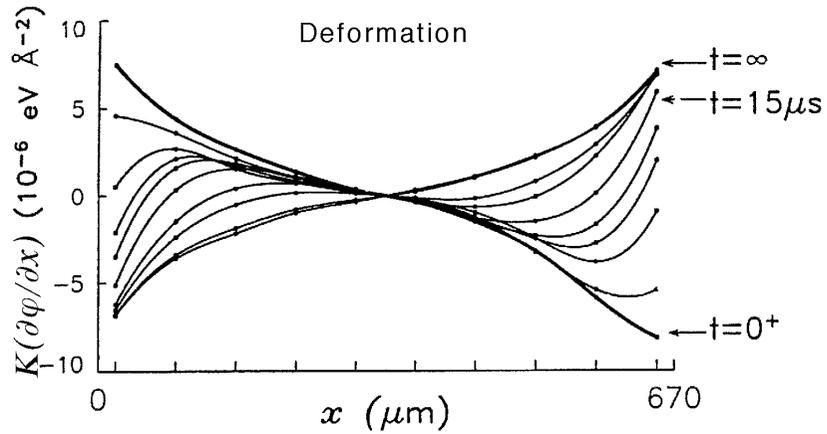
linear regime: assuming pinning of lateral growth of CDW wavefronts/dislocation loops



CDW current- and electrical field profile:



Brazovskii-model, application to multi-contact data by Adelman et al.:

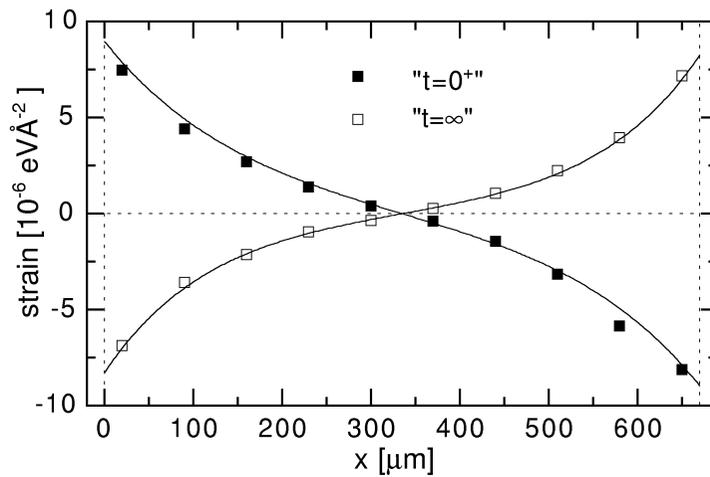


“short sample”

overlap of the two exponential decays coming from the two current contacts

$$\nabla\varphi \propto \exp\left(-\frac{x}{l}\right) - \exp\left(-\frac{L-x}{l}\right)$$

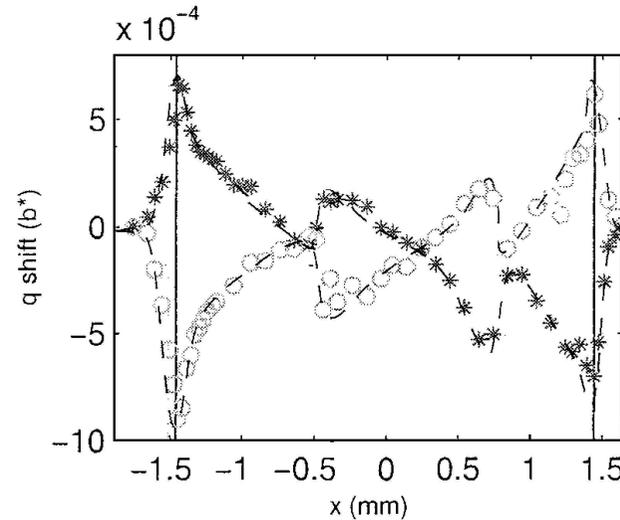
length scale: $l = 140 \pm 20 \mu\text{m}$



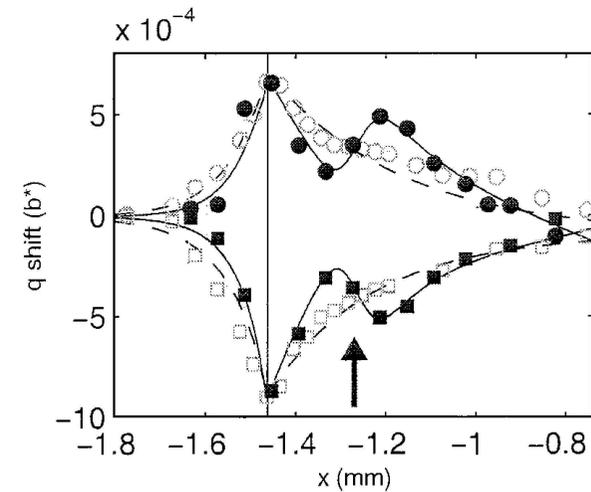
study by Rideau et al. (EPL 56 (2001) 289: CDW-deformation near defects

NbSe₃, T=90K, beam width: 20μm

- current contact very narrow (15μm): region beyond contact not “shunted” but with observable deformation $q \propto \nabla\phi$
- very steep decay of CDW deformation away from contact towards sample centre
- but at $x \approx -0.5$ and ≈ 0.85 significant deformation: sign of resumed current conversion to maintain charge transport across defect



- X-ray irradiation (30μm beam width) induced defect (arrow) gives rise to additional CDW deformation
=> additional current conversion centre
- length scale of effect on deformation: 75μm



Conclusion

- spatial dependences in CDW observed by various methods:
CDW-current profile, IR-transmission = indirect methods for CDW-strain measurements
high-resolution X-ray diffraction = direct observation of CDW-strain
- NbSe₃: current injection/extraction gives rise to CDW-deformation, decaying exponentially with distance from contact
- NbSe₃: CDW-deformation seems to be well described by Brazovskii-model
CDW-deformation due to charge disbalance
heterogeneous phase slip/current conversion
- defects and current contacts play similar role:
centres of current conversion, charge disbalance